MPSH81

PNP SILICON
RF TRANSISTOR



TO-92 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR MPSH81 is a PNP Silicon Transistor designed for general purpose RF amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Continuous Collector Current	I_C	50	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JC}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

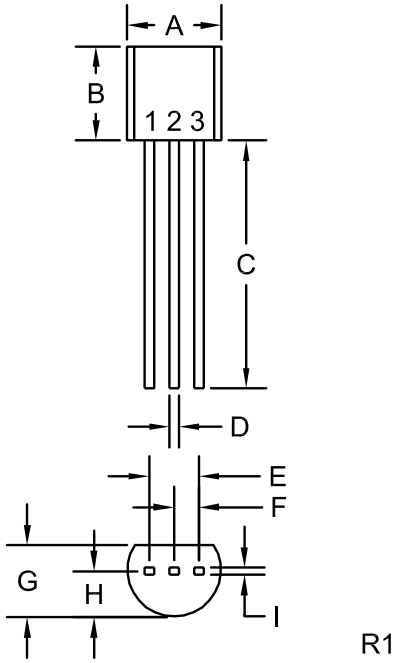
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=10V		100	nA
I_{EBO}	V_{EB}=2.0V		100	nA
BV_{CBO}	I_C=10μA	20		V
BV_{CEO}	I_C=1.0mA	20		V
BV_{EBO}	I_E=10μA	3.0		V
$V_{CE(SAT)}$	I_C=5.0mA, I_B=0.5mA		0.5	V
$V_{BE(ON)}$	V_{CE}=10V, I_C=5.0mA		0.9	V
h_{FE}	V_{CE}=10V, I_C=5.0mA	60		
f_T	V_{CE}=10V, I_C=5.0mA, f=100MHz	600		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		0.85	pF
C_{ib}	V_{CB}=10V, I_B=0, f=1.0MHz		0.65	pF

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TO-92 CASE - MECHANICAL OUTLINE



R1

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

LEAD CODE:
1) BASE
2) EMITTER
3) COLLECTOR

MARKING: FULL PART NUMBER

R0 (25-April 2008)